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Flat C, 1/F Shamshuipo Building 1A Shek Kip Mei Street Shamshuipo, Kowloon, Hong Kong

DF500 DC-FCVA PVD System







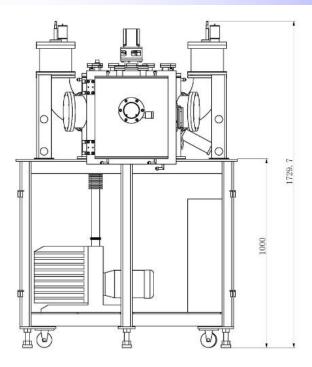
Model	DF 500
Chamber	SS 304 steel Φ500mm x 450mm; Double-wall with water cooling
Pumping System	Turbo-molecular pump 1300L/s and rotary pump 9L/s, throttle valve, pneumatic gate valve, foreline valve, roughing valve and venting valve
Ultimate Pressure	Better than 8 x 10^{-5} Pa; From Atm. to 10^{-4} Pa ≤ 30 min
Vacuum Measurement	2 thermal gauges and 1 ion gauge with control displayer
Gas Feeding	2 MFCs 100SCCM with controller (optional for 4)
Substrate Structure	4 sets of double rotary substrate holders (can be tailor made)
Substrate Rotation	Satellite rotation with adjustable speed of 0-10RPM
Chmber Heating	PID temperature from RT to 350°C±2°C by inserting heating bars with power ≥2kW
Substrate Bias	DC output (20V-100V), Pulse output (100V-1000V, 40kHz, 10%-80%) or DC superposed Pulse output
DC-FCVA Source	2 sets for DC FCVA arc sources (optional for 4 sets) 90° electromagnetic filter with scanning coil for vertical arc beam swaying Cathode dimension: BottomΦ71mm x Height50mm x TopΦ50mm; Auto electromechnical triggering; Arc discharge voltage: 30V-70V; Arc current: 20A-100A;
Interlock & Protection	Vacuum & cooling water interlock, over-current & over-voltage protection
Applications	Reactive deposition for nano-structured, nano-composited and multilayer of conductive, semi-conductive, insulating and opto-electrical films

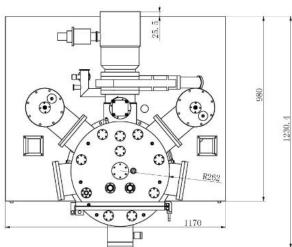


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The system has equipped with 2 sets of DC filtered cathodic vacuum arc DC-FCVA sources (able to install 4 sets) for thin film deposition. The DC-FCVA sources are used for high ionization ion reactive deposition. Two sources can be flexible operated under different discharge current to control the composition percentage during the deposition process. There also have 2 MFCs (optional for 4) to handle 2 types of gas species for reactive deposition. In additions, there are 4 revolution stages that the workpieces can be subjected to double rotary to achieve high uniform deposition where the treatment zone is upto ≥150mm. The ambient temperature of the chamber can be heated up to ~350°C and the workpieces can be Pulse/DC biased to obtain coatings with desirable properties.

